

PMEM1505NG

NPN transistor/Schottky rectifier module

Rev. 02 — 31 August 2009

Product data sheet

1. Product profile

1.1 General description

Combination of an NPN transistor with low V_{CEsat} and high current capability and a planar Schottky barrier rectifier with an integrated guard ring for stress protection in a SOT353 (SC-88A) small plastic package. PNP complement: PMEM1505PG

1.2 Features

- 300 mW total power dissipation
- Current capability up to 0.5 A
- Reduces printed-circuit board area required
- Reduces pick and place costs
- Small plastic SMD package
- Transistor
 - ◆ Low collector-emitter saturation voltage.
- Diode
 - ◆ Ultra high-speed switching
 - ◆ Very low forward voltage
 - ◆ Guard ring protected

1.3 Applications

- DC-to-DC converters
- General purpose load drivers
- MOSFET drivers
- Inductive load drivers
- Reverse polarity protection circuits

1.4 Quick reference data

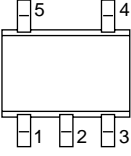
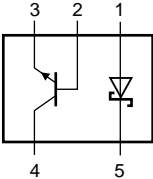
Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
NPN transistor						
V_{CEO}	collector-emitter voltage	open base	-	-	15	V
I_C	collector current (DC)	continuous	[1]	-	0.5	A
Schottky barrier rectifier						
V_R	continuous reverse voltage		-	-	20	V
I_F	continuous forward current		-	-	0.5	A

[1] Mounted on a FR4 printed-circuit board, single-sided copper, tin-plated, standard footprint for SOT353.

2. Pinning information

Table 2. Discrete pinning

Pin	Description	Simplified outline	Symbol
1	anode		
5	cathode		
4	collector		
2	base		
3	emitter		

sym023

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PMEM1505NG	-	plastic surface mounted package; 5 leads	SOT353

4. Marking

Table 4. Marking

Type number	Marking code ^[1]
PMEM1505NG	L7*

[1] * = p: made in Hong Kong

* = t: made in Malaysia

* = W: made in China

5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
NPN transistor					
V_{CBO}	collector-base voltage	open emitter	-	15	V
V_{CEO}	collector-emitter voltage	open base	-	15	V
V_{EBO}	emitter-base voltage	open collector	-	6	V
I_C	collector current (DC)	continuous	[1]	0.5	A
		continuous	[2]	0.6	A
		continuous; $T_s \leq 55\text{ °C}$	[3]	1	A
I_{CM}	peak collector current		-	1	A
I_{BM}	peak base current		-	100	mA

Table 5. Limiting values ...continued
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit	
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C [1]	-	200	mW	
		T _{amb} ≤ 25 °C [2]	-	250	mW	
		T _s ≤ 55 °C [3]	-	800	mW	
T _j	junction temperature		-	150	°C	
Schottky barrier rectifier						
V _R	continuous reverse voltage		-	20	V	
I _F	continuous forward current		-	0.5	A	
I _{FSM}	non-repetitive peak forward current	t = 8.3 ms; square wave	-	5	A	
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C [1]	-	100	mW	
		T _{amb} ≤ 25 °C [2]	-	200	mW	
		T _s ≤ 55 °C [3]	-	800	mW	
T _j	junction temperature		[2]	-	125	°C
Combined device						
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C [2]	-	300	mW	
T _{stg}	storage temperature		-65	+150	°C	
T _{amb}	operating ambient temperature		[2]	-65	+125	°C

- [1] Mounted on a FR4 printed-circuit board, single-sided copper, tin-plated, standard footprint for SOT353.
- [2] Device mounted on a printed-circuit board, single-sided copper, tin-plated, 1 cm² mounting pad for both collector and cathode.
- [3] Solder point of collector or cathode tab.

6. Thermal characteristics

Table 6. Thermal characteristics[1]

Symbol	Parameter	Conditions	Typ	Unit
Single device				
R _{th(j-s)}	thermal resistance from junction to solder point	in free air	[2] 120	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	in free air	[3] 395	K/W
			[4] 495	K/W
Combined device				
R _{th(j-a)}	thermal resistance from junction to ambient	in free air	[5] 410	K/W

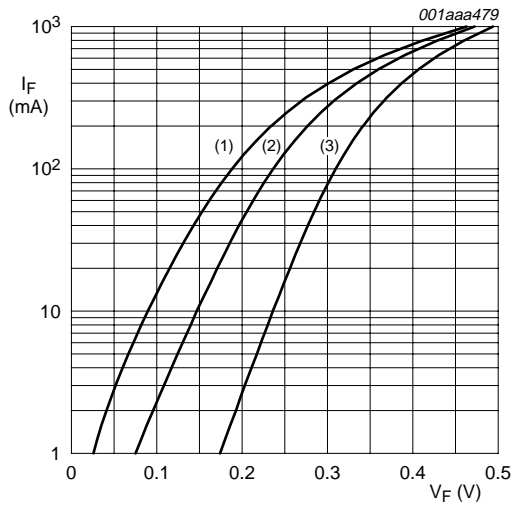
- [1] For Schottky barrier rectifiers thermal run-away has to be considered, as in some applications the reverse power losses P_R are a significant part of the total power losses. Nomograms for determining the reverse power losses P_R and I_{F(AV)} rating will be available on request.
- [2] Solder point of collector or cathode tab.
- [3] Device mounted on a printed-circuit board, single-sided copper, tin-plated, 1 cm² mounting pad for both collector and cathode.
- [4] Mounted on a FR4 printed-circuit board, single-sided copper, tin-plated, standard footprint for SOT353.
- [5] Mounted on a ceramic printed-circuit board, single-sided copper, tin-plated, standard footprint.

7. Characteristics

Table 7. Characteristics
T_{amb} = 25 °C unless otherwise specified

Symbol	Parameter	Conditions	Min	Typ	Max	Unit	
NPN transistor							
I _{CBO}	collector-base cut-off current	V _{CB} = 15 V; I _E = 0 A	-	-	100	nA	
		V _{CB} = 15 V; I _E = 0 A; T _j = 150 °C	-	-	50	μA	
I _{EBO}	emitter-base cut-off current	V _{EB} = 5 V; I _C = 0 A	-	-	100	nA	
h _{FE}	DC current gain	V _{CE} = 2 V; I _C = 10 mA	200	-	-		
		V _{CE} = 2 V; I _C = 100 mA	150	-	-		
		V _{CE} = 2 V; I _C = 500 mA	90	-	-		
V _{CEsat}	collector-emitter saturation voltage	I _C = 10 mA; I _B = 0.5 mA	-	-	25	mV	
		I _C = 200 mA; I _B = 10 mA	-	-	150	mV	
		I _C = 500 mA; I _B = 50 mA	-	-	250	mV	
R _{CEsat}	equivalent on-resistance	I _C = 500 mA; I _B = 50 mA	[1]	-	300	< 500 mΩ	
V _{BEsat}	base-emitter saturation voltage	I _C = 500 mA; I _B = 50 mA	[1]	-	-	1.1 V	
V _{BEon}	base-emitter turn-on voltage	V _{CE} = 2 V; I _C = 100 mA	[1]	-	-	0.9 V	
f _T	transition frequency	V _{CE} = 5 V; I _C = 100 mA; f = 100 MHz	250	420	-	MHz	
C _c	collector capacitance	V _{CB} = 10 V; I _E = I _e = 0 A; f = 1 MHz	-	4.4	6	pF	
Schottky barrier rectifier							
V _F	continuous forward voltage	see Figure 1					
		I _F = 10 mA	[1]	-	240	270	mV
		I _F = 100 mA	[1]	-	300	350	mV
		I _F = 500 mA	[1]	-	400	460	mV
I _R	reverse current	see Figure 2					
		V _R = 5 V	[1]	-	5	10	μA
		V _R = 8 V	[1]	-	7	20	μA
		V _R = 15 V	[1]	-	10	50	μA
C _d	diode capacitance	V _R = 5 V; f = 1 MHz; see Figure 3	-	19	25	pF	

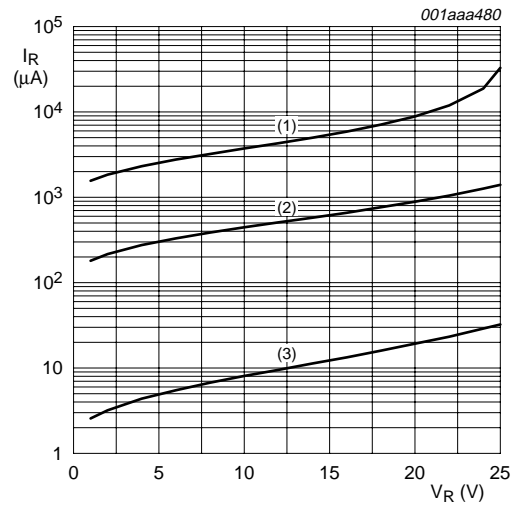
[1] Pulse test: t_p ≤ 300 μs; δ ≤ 0.02



Schottky barrier rectifier

- (1) $T_{amb} = 125\text{ °C}$
- (2) $T_{amb} = 85\text{ °C}$
- (3) $T_{amb} = 25\text{ °C}$

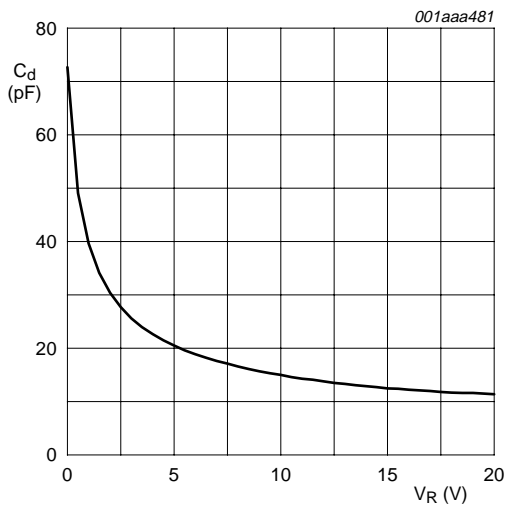
Fig 1. Forward current as a function of forward voltage; typical values



Schottky barrier rectifier

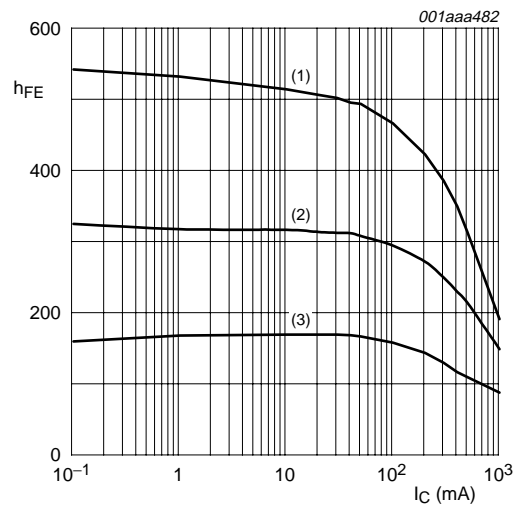
- (1) $T_{amb} = 125\text{ °C}$
- (2) $T_{amb} = 85\text{ °C}$
- (3) $T_{amb} = 25\text{ °C}$

Fig 2. Reverse current as a function of reverse voltage; typical values



Schottky barrier rectifier; $f = 1\text{ MHz}$; $T_{amb} = 25\text{ °C}$

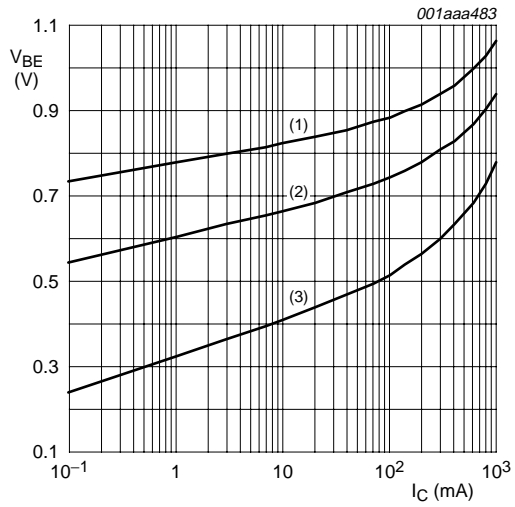
Fig 3. Diode capacitance as a function of reverse voltage; typical values



NPN transistor; $V_{CE} = 2\text{ V}$

- (1) $T_{amb} = 150\text{ °C}$
- (2) $T_{amb} = 25\text{ °C}$
- (3) $T_{amb} = -55\text{ °C}$

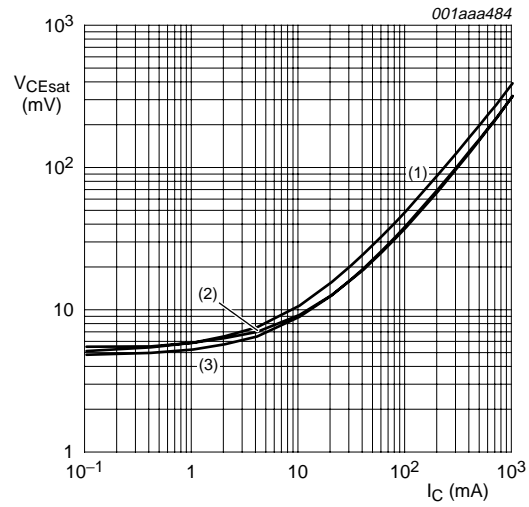
Fig 4. DC current gain as a function of collector current; typical values



NPN transistor; $V_{CE} = 2\text{ V}$

- (1) $T_{amb} = -55\text{ °C}$
- (2) $T_{amb} = 25\text{ °C}$
- (3) $T_{amb} = 150\text{ °C}$

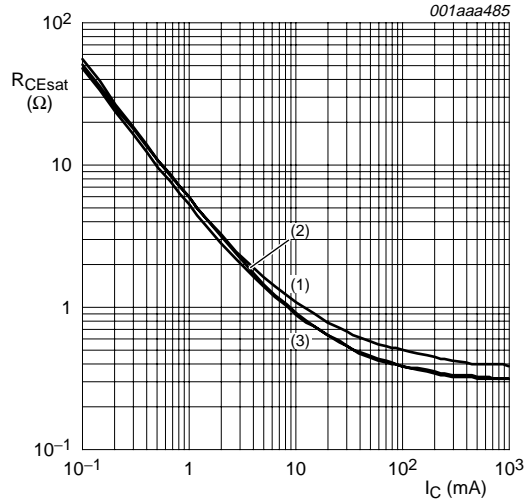
Fig 5. Base-emitter voltage as a function of collector current; typical values



NPN transistor; $I_C/I_B = 20$

- (1) $T_{amb} = 150\text{ °C}$
- (2) $T_{amb} = 25\text{ °C}$
- (3) $T_{amb} = -55\text{ °C}$

Fig 6. Collector-emitter saturation voltage as a function of collector current; typical values

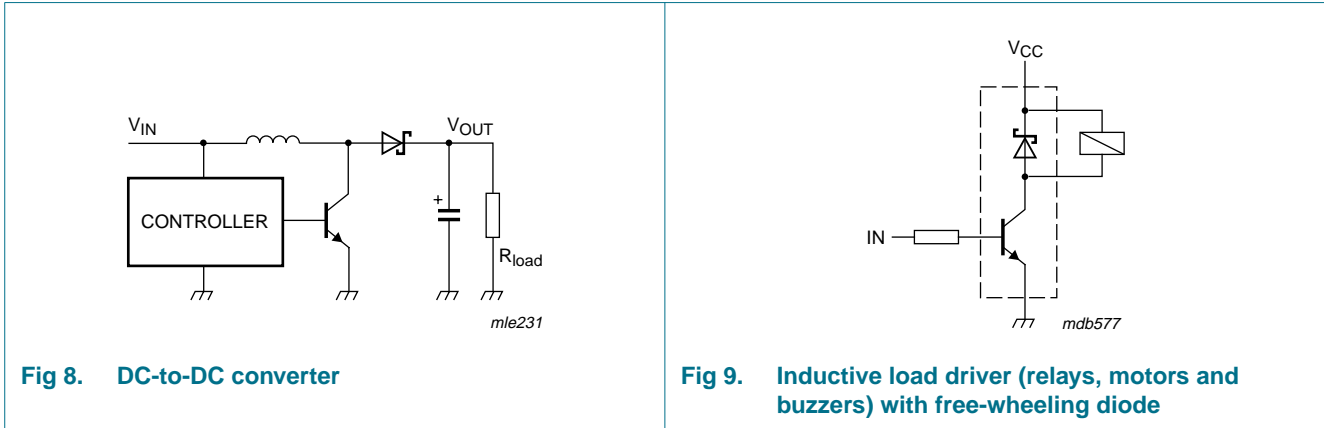


NPN transistor; $I_C/I_B = 20$

- (1) $T_{amb} = 150\text{ °C}$
- (2) $T_{amb} = 25\text{ °C}$
- (3) $T_{amb} = -55\text{ °C}$

Fig 7. Equivalent on-resistance as a function of collector current; typical values

8. Application information



9. Package outline

Plastic surface-mounted package; 5 leads

SOT353

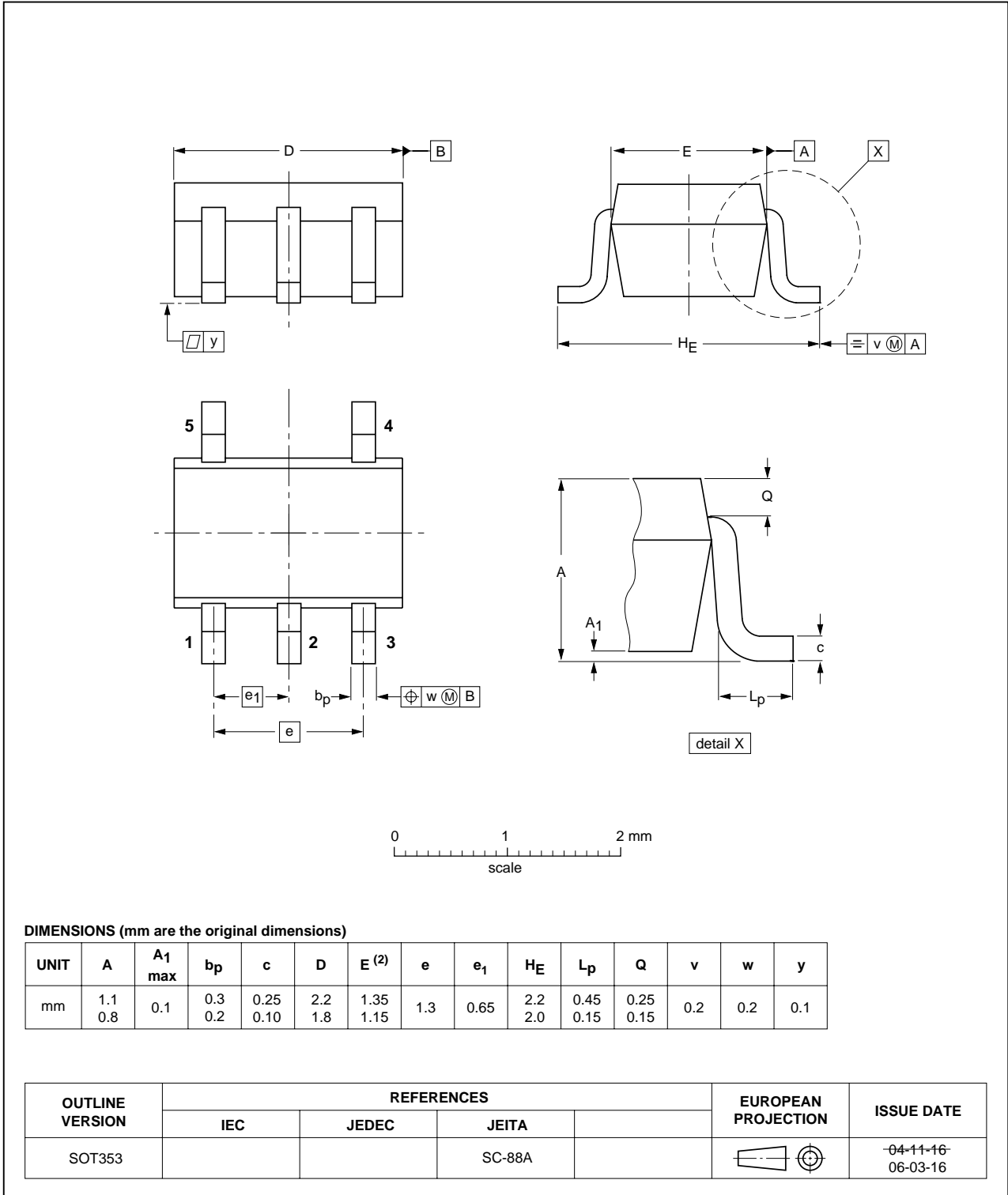


Fig 10. Package outline

10. Revision history

Table 8. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PMEM1505NG_2	20090831	Product data	-	PMEM1505NG_1
Modifications:		<ul style="list-style-type: none">• This data sheet was changed to reflect the new company name NXP Semiconductors, including new legal definitions and disclaimers. No changes were made to the technical content.• Table 2 “Discrete pinning”: amended• Figure 10 “Package outline”: updated		
PMEM1505NG_1	20040525	Product data	-	-

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11.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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